

IN THE CLAIMS

1. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate including a source region and drain region at its surface;

a gate electrode formed ~~on said semiconductor substrate including~~ so as to include a straight portion separating said source region and said drain region on said semiconductor substrate;

a dummy electrode formed at a position on an extension of a longitudinal direction of said gate electrode ~~straight portion on said semiconductor substrate~~;

a stopper insulating film, each overlying said gate electrode and said dummy electrode;

a sidewall insulating film covering a side of said gate electrode, said dummy electrode and said stopper insulating film;

an interlayer insulating film ~~covering a top surface of~~ formed on said semiconductor substrate to cover up said sidewall insulating film and said stopper insulating film; and

a linear contact portion defined by a conductive member extending ~~from~~ vertically ~~within~~ in said interlayer insulating film and electrically connected to one of said source region and said drain region at its bottom end, said linear contact portion ~~being, when viewed from above,~~ extending ~~along~~ parallel to said straight portion of said gate electrode,

~~each longer side of a rectangle defined by said linear contact portion being, when viewed from above, located beyond said sidewall insulating film and within a top region of said gate electrode and said dummy electrode, and~~

~~a gap between said gate electrode and said dummy electrode appearing, when viewed from above, in said linear contact portion being filled with said sidewall insulating film such that said semiconductor substrate is not exposed~~

said linear contact portion extending to above said dummy electrode.

2. (Currently Amended) The semiconductor device of claim 1, wherein ~~said gate electrode is arranged in plurality parallel to each other and, when viewed from above, one of said source region and said drain region constitute a group of regions of a specified type defined as regions between adjacent two of said gate electrodes being discrete linearly with an isolation insulating film therebetween, and said linear contact portion extends to integrally cover said group of regions of the specified type, in a plan view, each longer side of a rectangle defined by said linear contact portion is located beyond said sidewall insulating film and within a top region of said gate electrode and said dummy electrode, and~~

a gap between said gate electrode and said dummy electrode is filled with said sidewall insulating film.

3. (Currently Amended) The semiconductor device of claim 2, ~~wherein said one of said source region and said drain region is electrically connected, via said linear contact portion, to a first interconnection extending, above said linear contact portion, parallel to said straight portion, and the other of said source region and said drain region is electrically connected to a second interconnection extending, above said gate electrode, perpendicularly to said straight portion of said gate electrode 1, wherein said gate electrode is arranged in plurality parallel to each other and one of said source region and said drain region constitutes a group of regions of a specified type defined in regions between adjacent two of said gate electrodes being discrete with an isolation insulating film therebetween, and said linear contact portion extends to integrally cover said group of regions of the specified type.~~

4. (New) The semiconductor device of claim 3, wherein said one of said source region and said drain region is electrically connected, via said linear contact portion, to a first interconnection extending, above said linear contact portion, parallel to said straight portion, and the other one of said source region and said drain region is electrically connected to a second interconnection extending, above said gate electrode, transversely to said straight portion of said gate electrode.